

Silicon NPN Power Transistors

2SC2361

DESCRIPTION

- With TO-220C package
- Complement to type 2SA1123
- Low collector saturation voltage

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

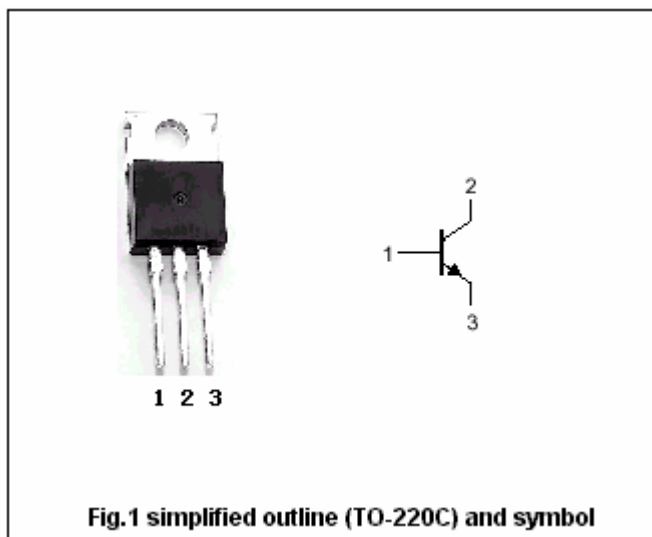


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	70	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current (DC)		4	A
P _C	Collector dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A; I _B =0	70			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1m A; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			1.5	V
V _{BE}	Base-emitter on voltage	I _C =3A ; V _{CE} =4V			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =2.5A ; V _{CE} =3V	50		240	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		70		MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)